NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV57** is Designed for use as push-pull amplifier, primarily in linear UHF TV transmitting Applications.

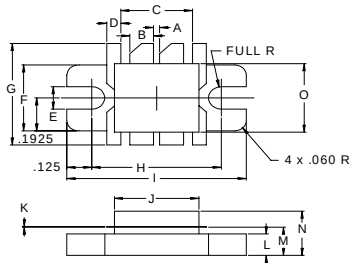
FEATURES:

- Input Matching Network
- Common emitter
- ***Omnigold***™ Metalization System with eutectic die bonding

MAXIMUM RATINGS

I_C	2.0 A
V_{CESM}	50 V
V_{CE}	27 V
P_{DISS}	77 W @ T_C = 25 C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.27 °C/W

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

ORDER CODE: ASI10646

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 25 mA	27			V
BV_{CES}	I_C = 10 mA	50			V
BV_{EBO}	I_E = 5.0 mA	3.5			V
I_{CES}	V_E = 27 V			10	mA
h_{FE}	V_{CE} = 25 V I_C = 850 mA	15			---
f_T	V_{CB} = 25 V I_E = 1.7 A V_{CB} = 25 V I_E = 850 mA		2.5 2.5		GHz
P_G IMD_1	V_{CE} = 25 V I_C = 850 mA f = 860 MHz P_{OUT} = 6.0 W	8.0 -60			dB dBc